

DFN2×2B-6L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a DFN2×2B-6L Plastic Package.

 $V_{DS} (V) = 30V$ $I_D = 14.7A$ ($V_{GS} = \pm 20V$)

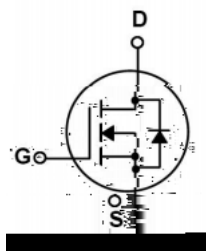
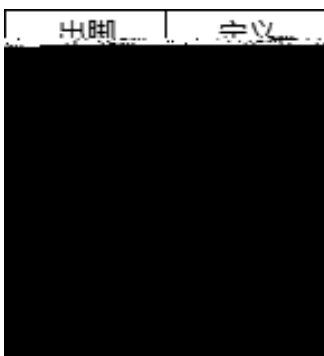
 $R_{DS(ON)} @ 10V < 7m\Omega$ (Typ. $6.3m\Omega$)

 $R_{DS(ON)} @ 4.5V < 12m\Omega$ (Typ. $9.5m\Omega$)

HF Product.

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

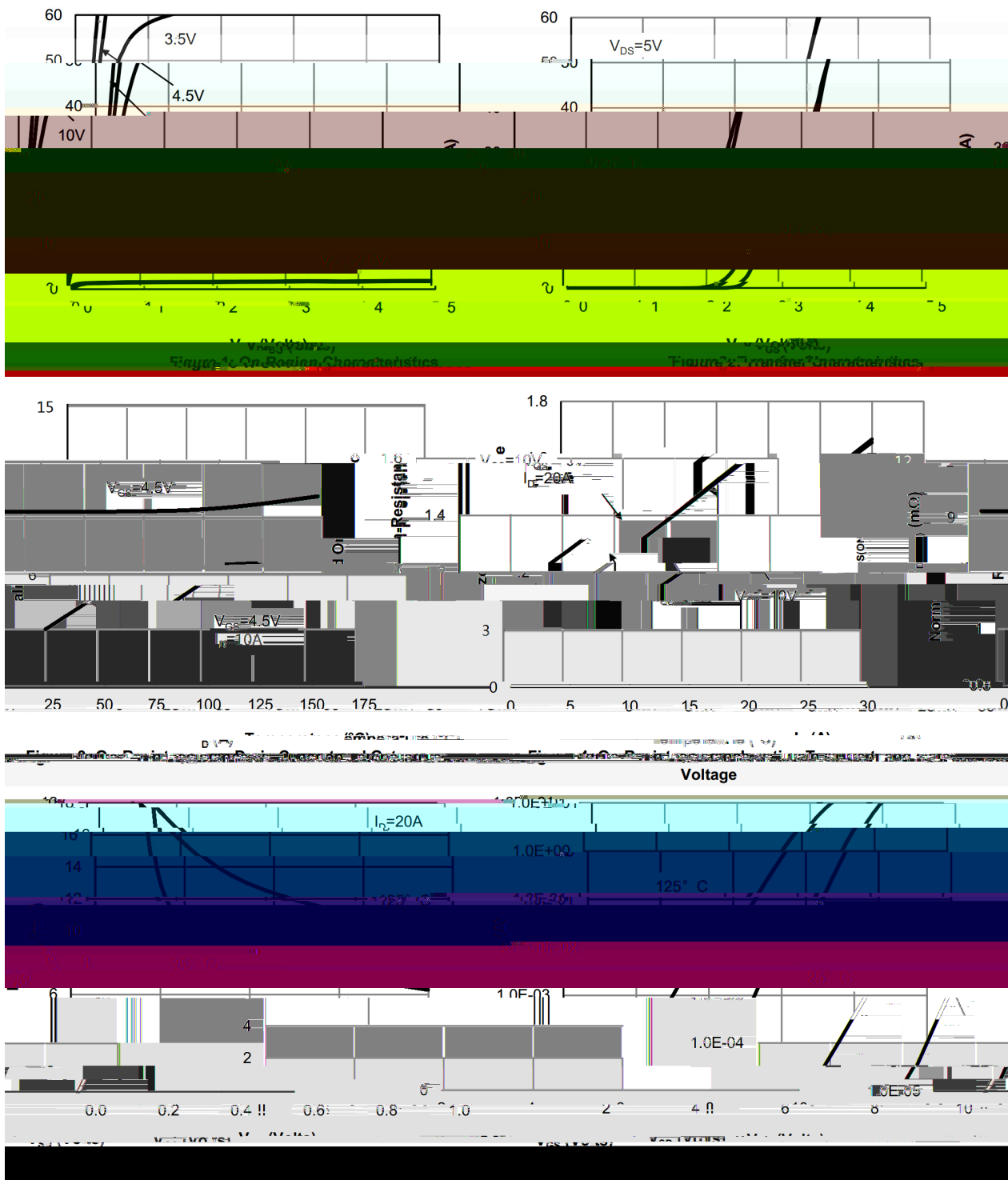


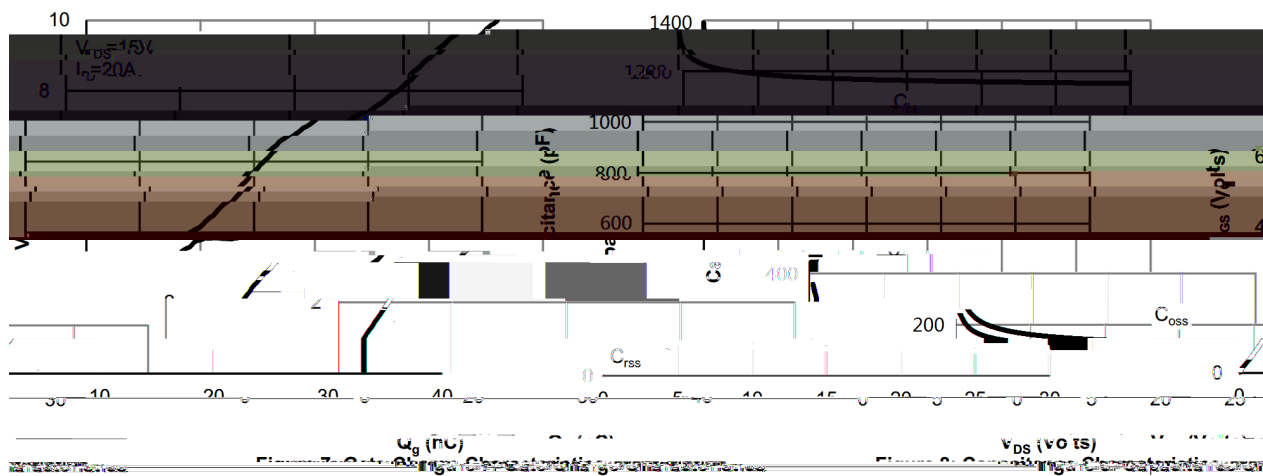
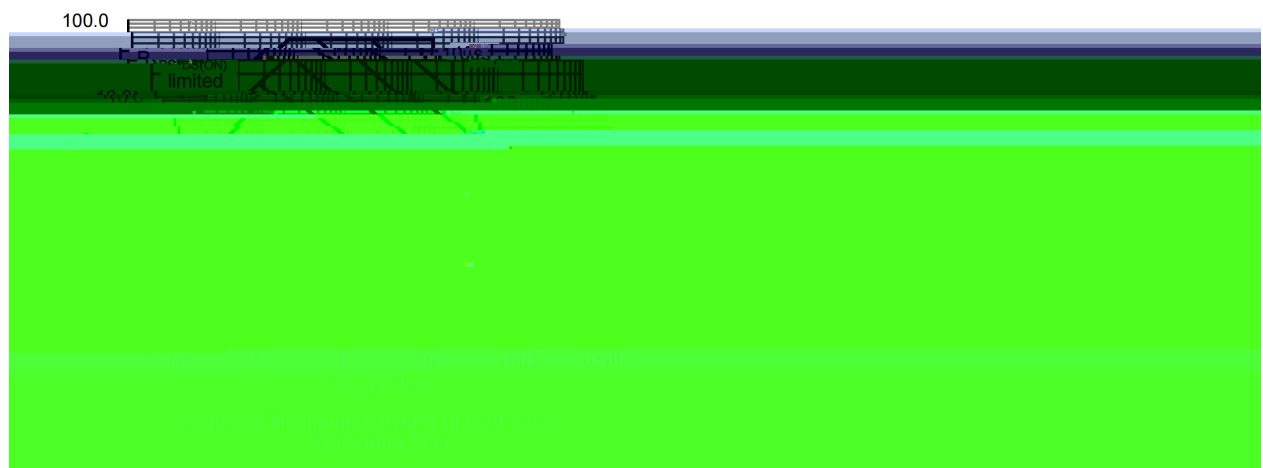
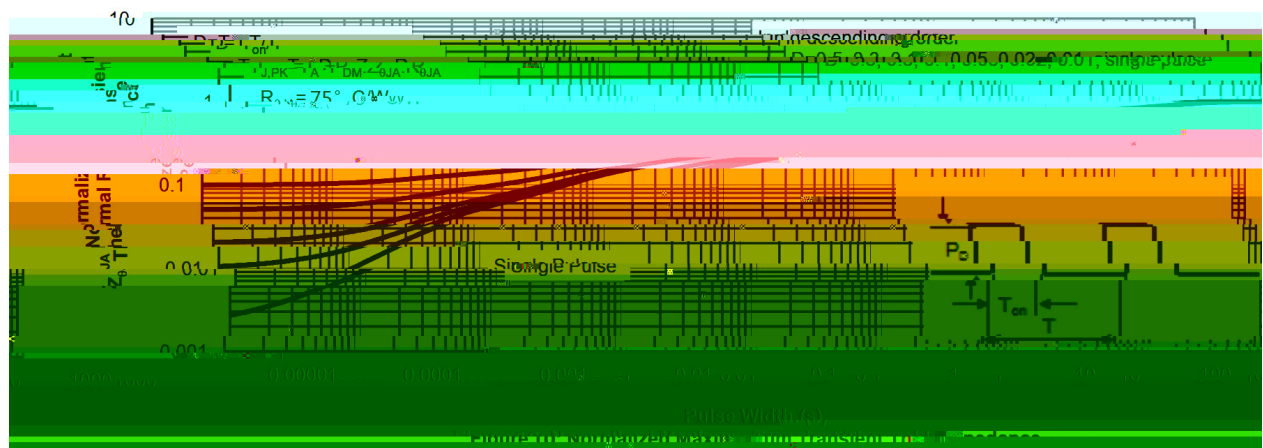
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Drain Current	I_D	14.7	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D		

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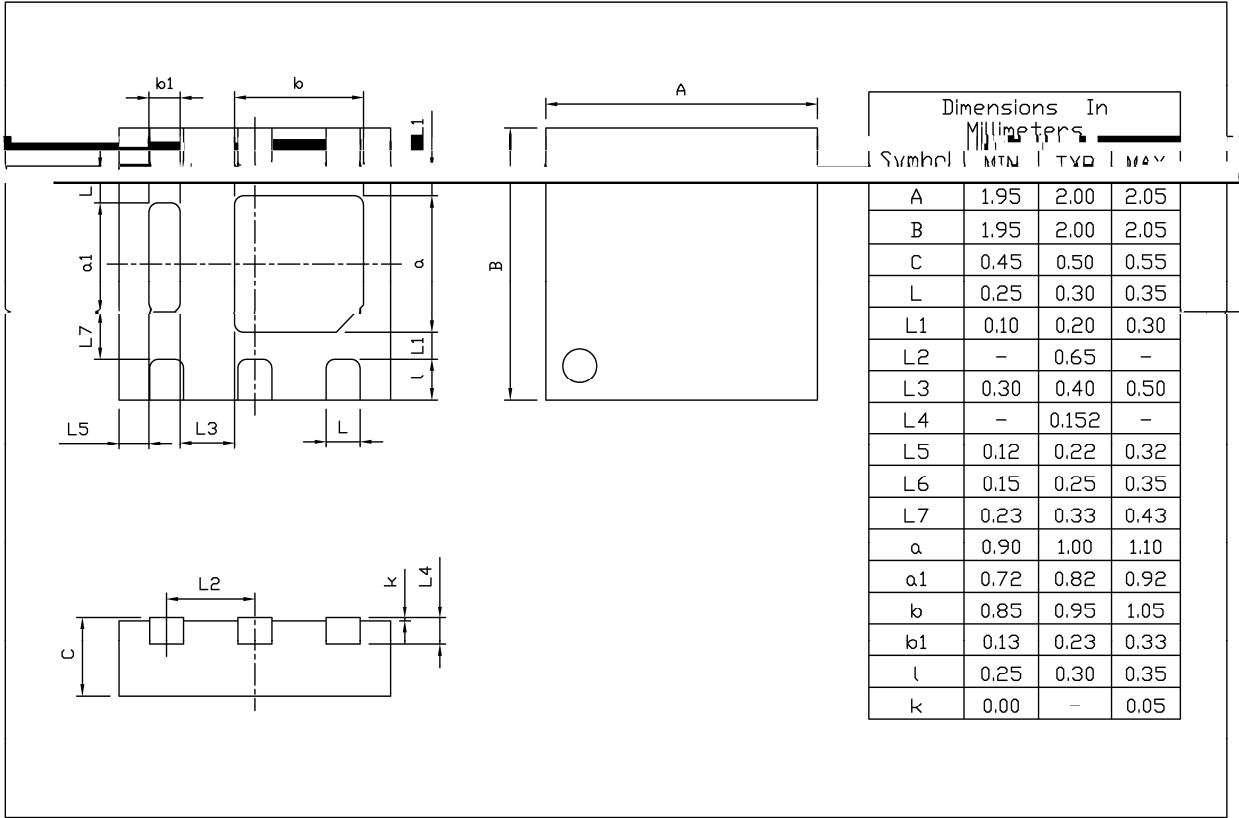
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15\text{ V}$ $R_L=0.75\Omega$ $V_{GS}=10\text{V}$ $R_{GEN}=3\Omega$		11		ns
Turn-On Rise Time	t_r			14		ns
Turn-Off Delay Time	$t_{d(off)}$			38		ns
Turn-Off Fall Time	t_f			10		ns



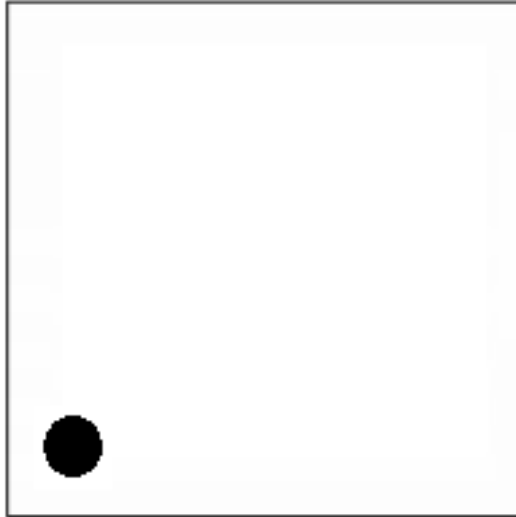


DFN2 X2B-6L-0.5

Unit:mm



Rev.01 202006



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